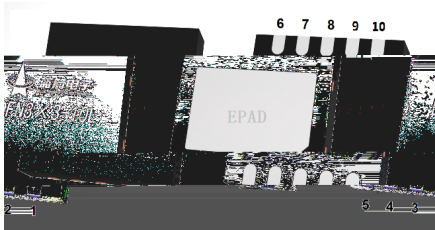


/ Pinning



Pin Number	Pin Name	Pin Description
1	VDD	
2,3,4,5	GND	
6,7,8,9,10	VM	
EPAD	GND	

/ Marking

See Marking Instructions.

/ Absolute Maximum Ratings(Ta=25)

/Parameter	/Symbol	/Value	/Unit
V _{DD} input pin voltage	V _{IN}	-0.3 to +8	V
V _{VM} input pin voltage	V _{VM}	-8 to +10	V
Maximum Junction Temperature	T _J	-40 to +145	
Storage Temperature	T _{stg}	-55 to +145	
ESD HBM Mode	ESD	4000	V

/ Electrical Characteristics(Unless otherwise specified,Ta=25)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Power supply						
Supply Voltage	V _{DD}		0		6	V
Charger input voltage	V _M		-6		6	V
Detection voltage						
Overcharge Detection Voltage	V _{OCV}		4.25	4.3	4.35	V
Overcharge Release Voltage	V _{OCR}		4.04	4.10	4.16	V
Overdischarge Detection Voltage	V _{ODV}		2.30	2.40	2.50	V
Overdischarge Release Voltage	V _{ODR}		2.90	3.00	3.10	V
Detection current						
Overdischarge Current Detection	I _{OCI}		18	23	28	A
Load Short-Circuiting Detection	I _{SHORT}		30	50	70	A
Overcharge Current Detection	I _{CHA}		14	20	26	A
Static current						
Current Consumption in Normal Operation	I _{OPE}	V _M =0V		3.5	7	μA
Current Consumption in Dormancy	I _{PDN}	V _{DD} =1.8V		2	6	μA
Pull-up and Pull-down Current from VM						
Internal pull-up current	I _{PU}			14		μA
Internal pull-down current	I _{PD}	V _M =1V		14		μA
Equivalent FET on Resistance						
Equivalent FET on Resistance	R _{DS}	I _{VM} =1A	6	9.5	11	mΩ

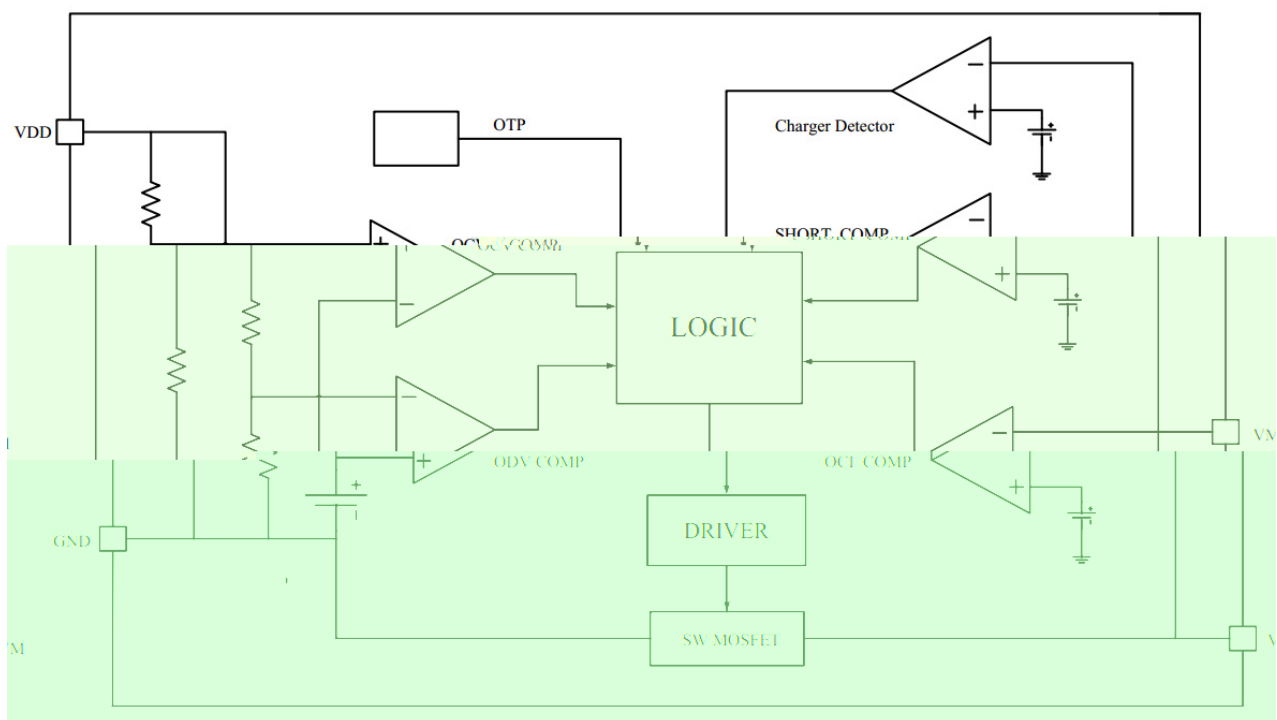
/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Over temperature protection						
Over-temperature protection	OTP			145		
Over-temperature protection release temperature	OTPR			120		
Detection delay						
Overcharge Voltage Detection Delay Time	T _{OCV}			100		ms
Overdischarge Voltage Detection Delay Time	T _{ODV}			100		ms
Overdischarge Current1 Detection Delay Time	T _{IOV1}			8		ms
Overdischarge Current2 Detection Delay Time	T _{IOV2}			2		ms
Load Short-Circuiting Detection Delay Time	T _{SHORT}			150		μs

* (OTP)

OTPR

*

/ FunctionI Block Diagram


/ Functional Description

BRCL3120CZV		
	MOSFET	10mΩ
BRCL3120CZV		

/ Normal Operating mode

/ Overcharge Voltage Condition

			(V _{OCV})	
(T _{OCV})	BRCL3120CZV	MOSFET		
	(T _{OCV})			
1	VM		(V _{CHA})	(V _{OCR})
2			(V _{OCV})	

/ Overcharge Current Condition

	I _{CHA}	(T _{OCI})	MOSFET
	BRCL3120CZV		

/ Overdischarge Voltage Condition

			(V _{ODV})	
(T _{ODV})	BRCL3120CZV			
	MOSFET		VDD	2.3V ()
	(I _{PDN}).		VDD	2.4V ()
			(V _{ODR})	BRCL3120CZV

/ Overdischarge Current Condition

			VM
VM			

/ Load Short-circuiting Condition

VM	(V _{SHORT})
T _{SHORT}	VM

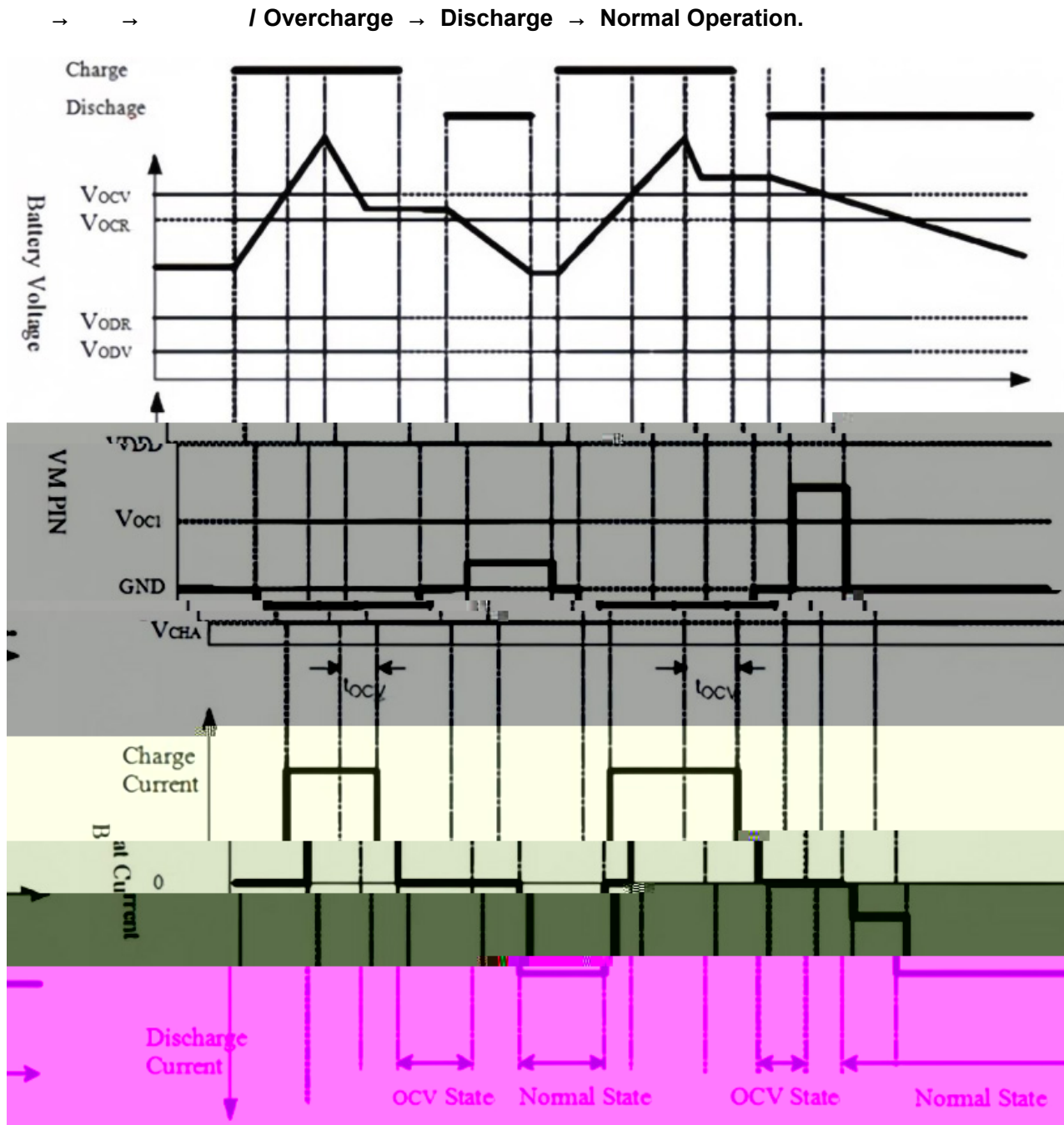
/ Charger Detection

V_M (V_{CHA})
 (V_{ODV}) BRCL3120CZV

0V / 0V Battery Charging Function

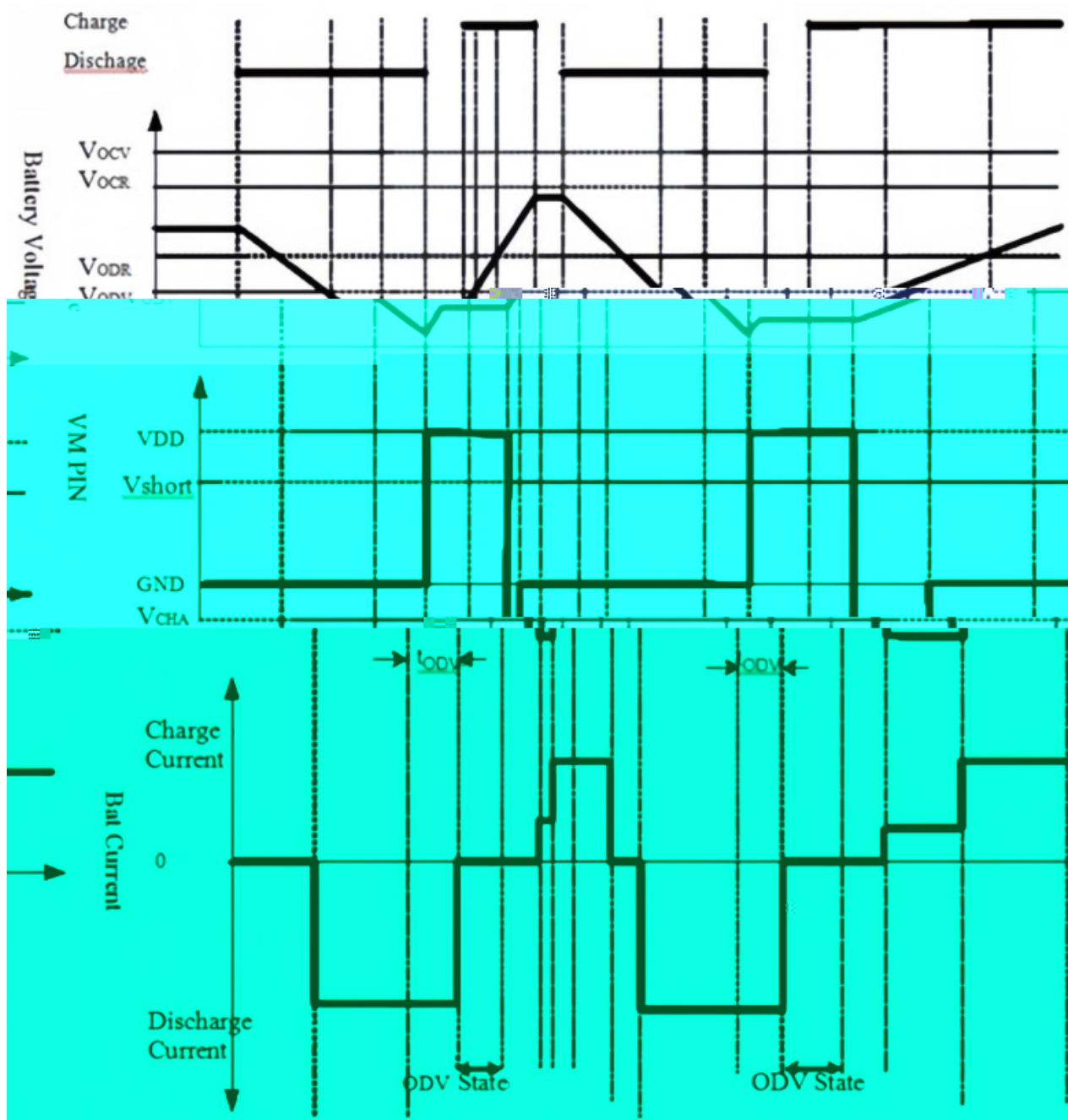
0V 2.3V 2.3V 200mA MOS

/ Timing Chart



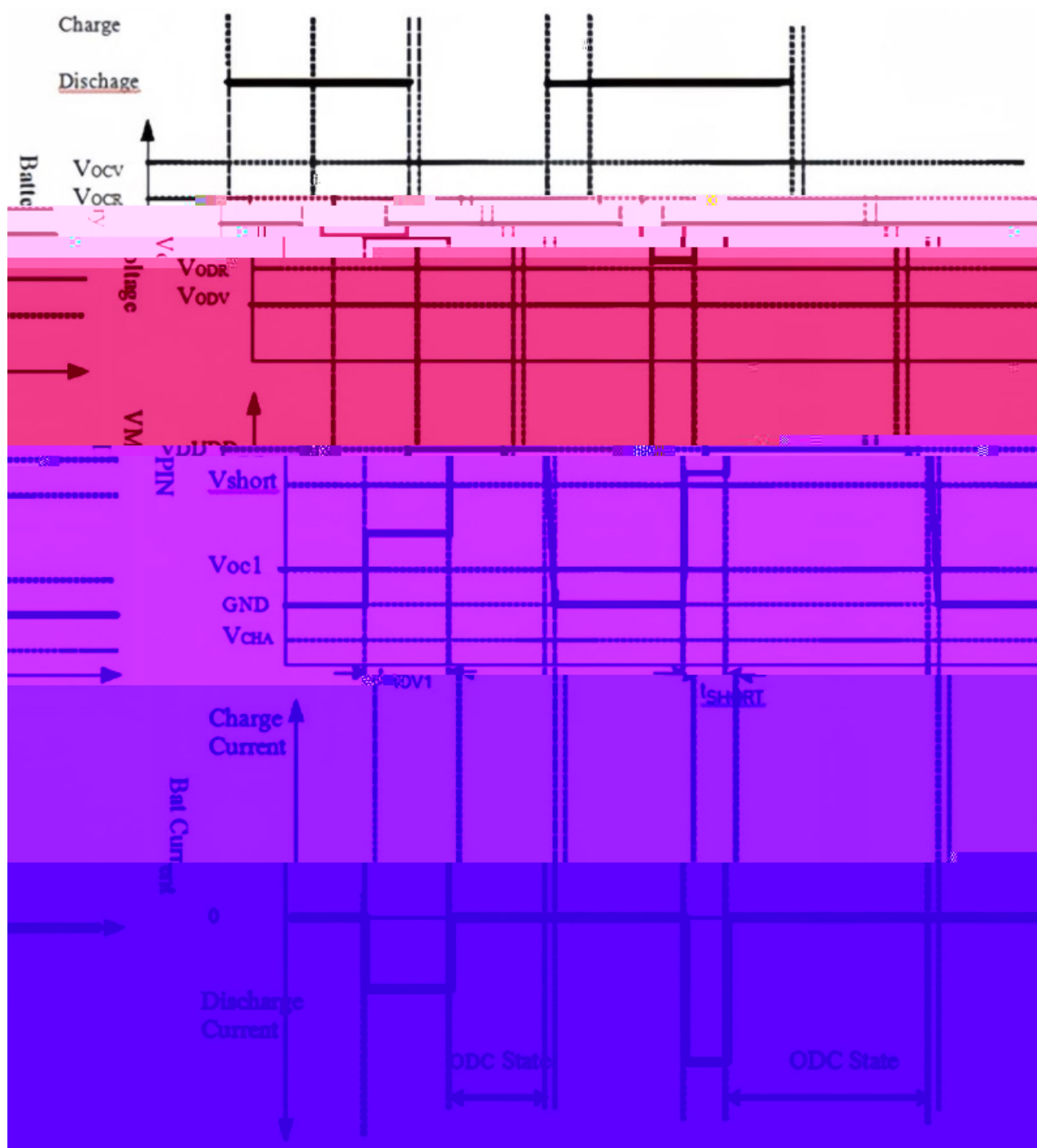
/ Timing Chart

→ / Overdischarge → Charging → Normal Operation.



/ Timing Chart

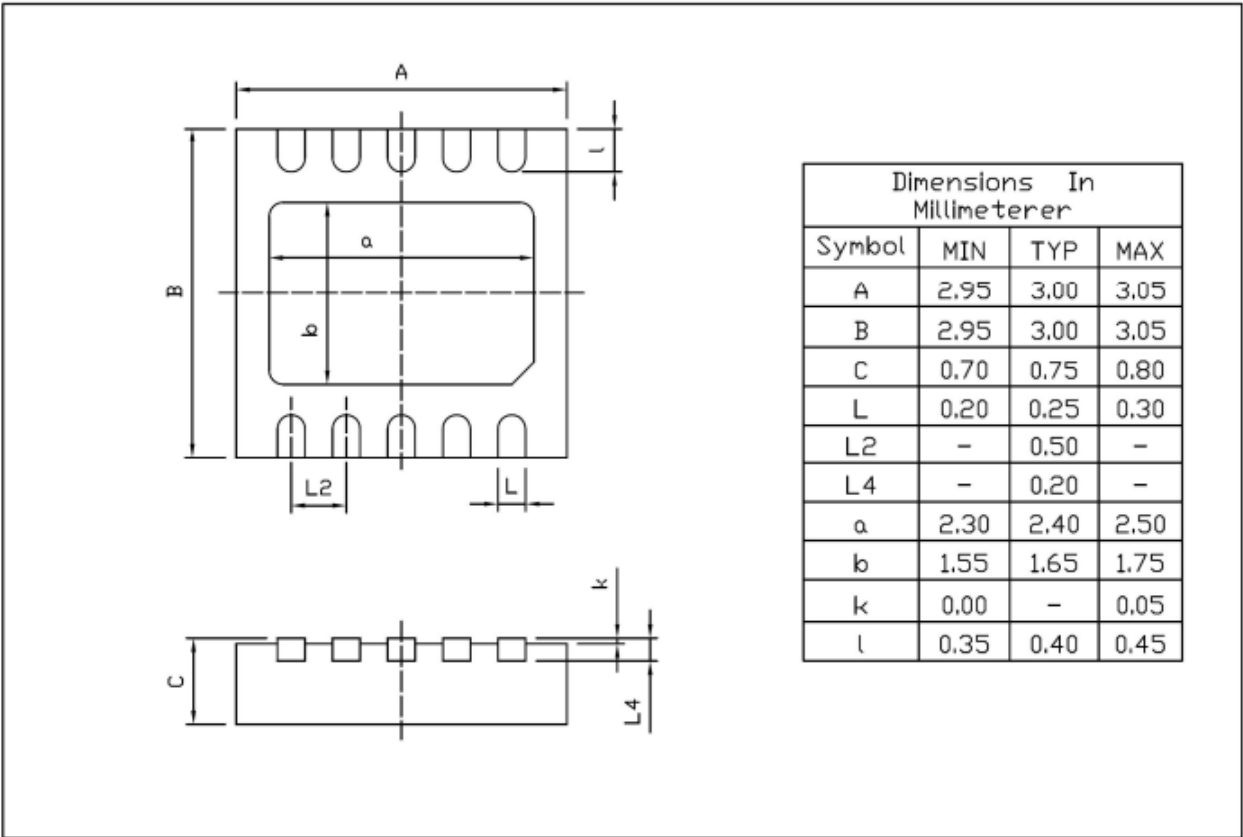
→ / Discharge Overcurrent → Normal Operation.



/ Package Dimensions

DFN3X3-10L

Unit:mm



Rev.00 202008

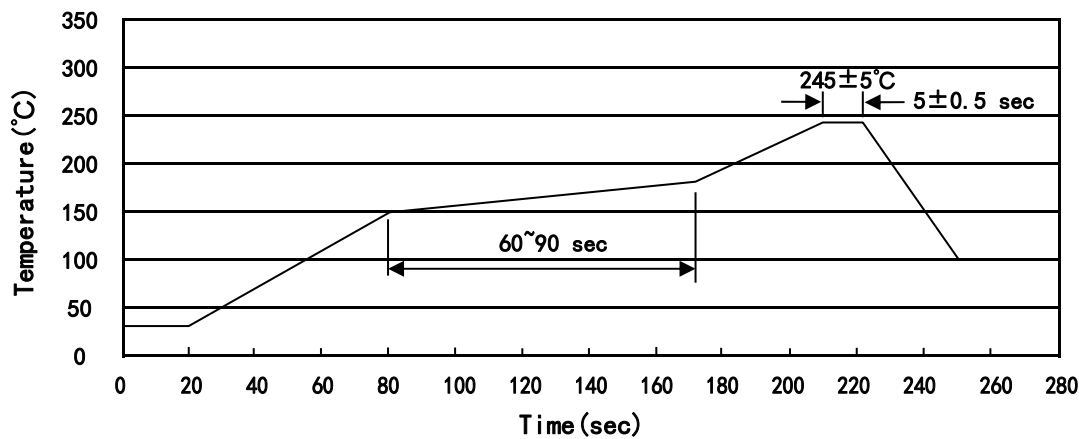
/ Marking Instructions



BR

3120C

() / Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

- | | | | | | |
|---|-------|-----|----|-----------|---|
| 1 | 150 | 180 | 60 | 90sec; | 1.Preheating:150~180 , Time:60~90sec. |
| 2 | 245±5 | | | 5±0.5sec; | 2.Peak Temp.:245±5 , Duration:5±0.5sec. |
| 3 | | | 2 | 10 /sec. | 3. Cooling Speed: 2~10 /sec. |

/ Resistance to Soldering Heat Test Conditions

260±5 10±1 sec. Temp.:260±5 Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
DFN3×3-10L	5,000	2	10,000	6	60,000	13 ×12	360×360×50	380×335×366

/ Notices

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